

isc Silicon NPN Darlington Power Transistor

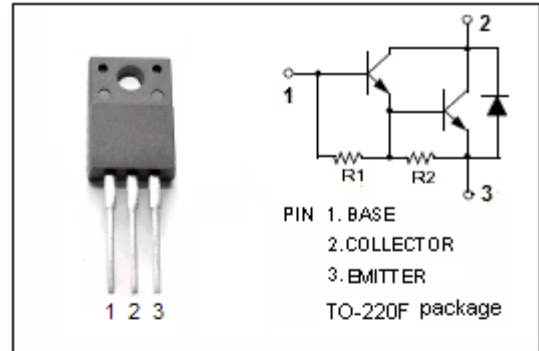
2SD1826

DESCRIPTION

- High DC Current Gain-
: $h_{FE} = 2000(\text{Min}) @ (V_{CE} = 2V, I_C = 3.5A)$
- Large Current Capability and Wide ASO.
- Complement to Type 2SB1224

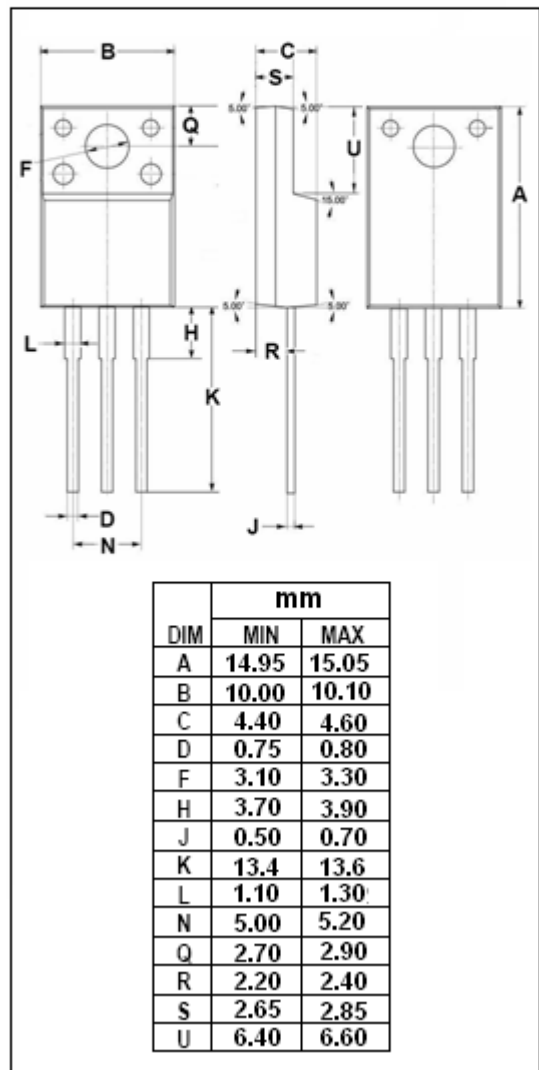
APPLICATIONS

- Designed for use in control of motor drivers, printer hammer drivers, relay drivers, and constant-voltage regulators.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	70	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	7	A
I_{CM}	Collector Current-Peak	10	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	25	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon NPN Darlington Power Transistor**2SD1826****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 50mA; R _{BE} = ∞	60			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 5mA; I _E = 0	70			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 3.5A; I _B = 7mA			1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 3.5A; I _B = 7mA			2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40V; I _E = 0			100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			3.0	mA
h _{FE}	DC Current Gain	I _C = 3.5A; V _{CE} = 2V	2000			
f _T	Current-Gain—Bandwidth Product	I _C = 3.5A; V _{CE} = 5V		20		MHz

Switching Times

t _{on}	Turn-on Time	I _C = 3A, I _{B1} = -I _{B2} = 6mA, V _{CC} = 20V; R _L = 6.7 Ω		0.6		μ s
t _{stg}	Storage Time			3.0		μ s
t _f	Fall Time			1.7		μ s